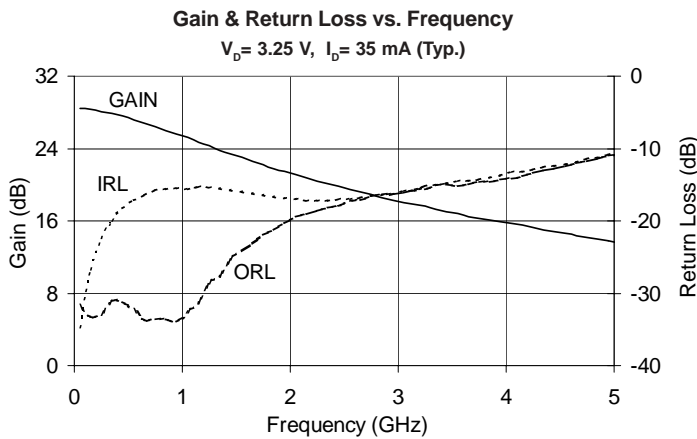




## Product Description

The SGA-3563 is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring 1 micron emitters provides high  $F_T$  and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in high suppression of intermodulation products. Operation requires only a single positive voltage supply, 2 DC-blocking capacitors, a bias resistor and an RF choke.

The matte tin finish on Sirenza's lead-free "Z" package is applied using a post annealing process to mitigate tin whisker formation and is RoHS compliant per EU Directive 2002/95. The package body is manufactured with green molding compounds that contain no antimony trioxide or halogenated fire retardants.



## SGA-3563

**SGA-3563Z** RoHS Compliant & Green Package

## DC-5000 MHz Silicon Germanium Cascadable HBT MMIC Amplifier



### Product Features

- Available in Lead Free, RoHS Compliant green package ( Z Suffix )
- 50 Ohm Cascadable Gain Block
- High Gain: 25.5 dB typ. at 850 MHz
- High Output IP3: 24.5 dBm typ. at 1950 MHz
- Low Noise Figure: 2.7 dB typ. at 1950 MHz
- Low Current Draw: 35mA typ.
- Single Voltage Supply Operation

### Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Symbol	Parameter	Freq. (MHz)	Min.	Typ.	Max.	Units
G	Small Signal Gain	850 1950 2400	23.5 19.5	25.5 21.5 20.0	27.5 23.5	dB
$P_{1dB}$	Output Power at 1dB Compression	850 1950	11.0	13.0 12.5		dBm
$OIP_3$	Output Third Order Intercept Point (Tone Spacing = 1 MHz, Pout per tone = -5 dBm )	850 1950	22.5	24.0 24.5		dBm
Bandwidth	Determined by Return Loss (>10dB)			5000		MHz
IRL	Input Return Loss	1950	11.2	15.5		dB
ORL	Output Return Loss	1950	11.2	20.0		dB
NF	Noise Figure	1950		2.7	3.7	dB
$V_D$	Device Operating Voltage		3.0	3.25	3.5	V
$I_b$	Device Operating Current		31	35	39	mA
$R_{TH}$ , j-l	Thermal Resistance (junction to lead)			255		°C/W

**Test Conditions:**  $I_b = 35\text{ mA}$  (Typ.)  $T_{LEAD} = 25^\circ\text{C}$   $Z_s = Z_L = 50\text{ Ohms}$

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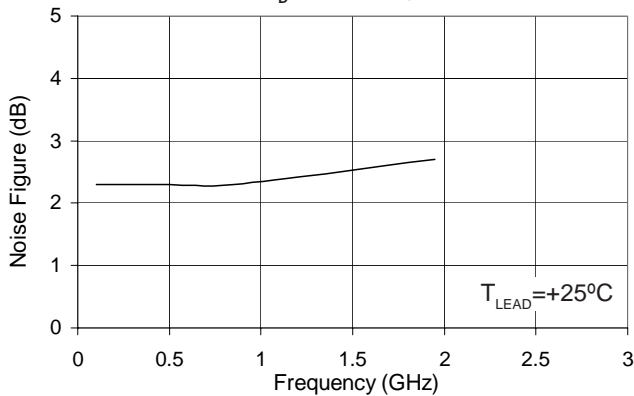
**Typical RF Performance at Key Operating Frequencies**

Symbol	Parameter	Units	Frequency (MHz)					
			100	500	850	1950	2400	3500
G	Small Signal Gain	dB	28.5	27.5	25.5	21.5	20.0	17.0
OIP <sub>3</sub>	Output Third Order Intercept Point	dBm	24.0	23.6	24.0	24.5	24.0	22.0
P <sub>1dB</sub>	Output Power at 1dB Compression	dBm	13.0	13.0	13.0	12.5	12.0	10.0
IRL	Input Return Loss	dB	29.7	17.6	15.6	15.5	17.2	14.7
ORL	Output Return Loss	dB	31.8	31.1	33.6	20.0	17.9	15.0
S <sub>12</sub>	Reverse Isolation	dB	29.4	29.3	28.6	25.5	23.9	21.3
NF	Noise Figure	dB	2.3	2.3	2.3	2.7		

Test Conditions: I<sub>b</sub> = 35 mA (Typ.) T<sub>LEAD</sub> = 25°C Z<sub>S</sub> = Z<sub>L</sub> = 50 Ohms Tone Spacing = 1 MHz Pout per tone = -5 dBm

**Noise Figure vs. Frequency**

I<sub>b</sub> = 35 mA (Typ.)



**Absolute Maximum Ratings**

Parameter	Absolute Limit
Max. Device Current (I <sub>b</sub> )	70 mA
Max. Device Voltage (V <sub>b</sub> )	6 V
Max. RF Input Power	+18 dBm
Max. Junction Temp. (T <sub>J</sub> )	+150°C
Operating Temp. Range (T <sub>L</sub> )	-40°C to +85°C
Max. Storage Temp.	+150°C

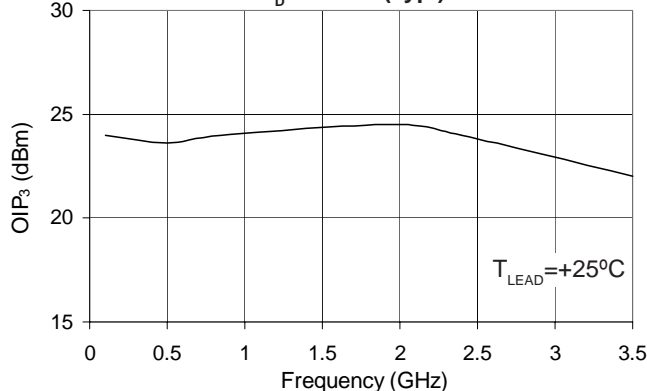
Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.

Bias conditions should also satisfy the following expression:

$$I_b V_D < (T_J - T_L) / R_{TH} \cdot j$$

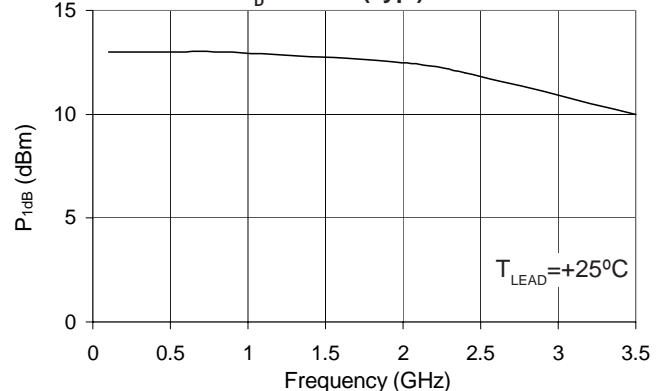
**OIP<sub>3</sub> vs. Frequency**

I<sub>b</sub> = 35 mA (Typ.)

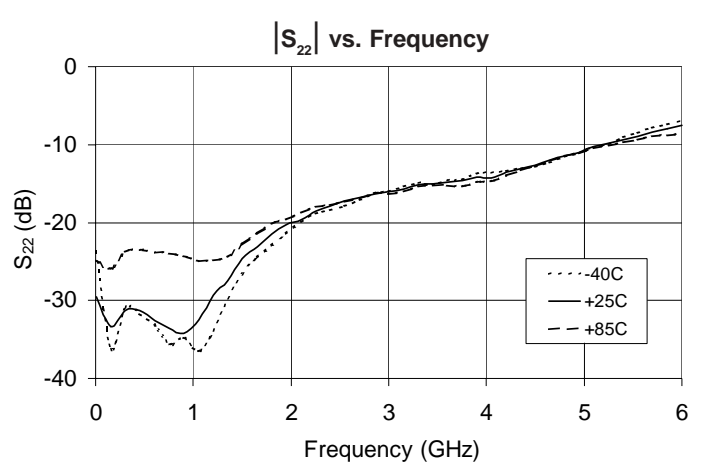
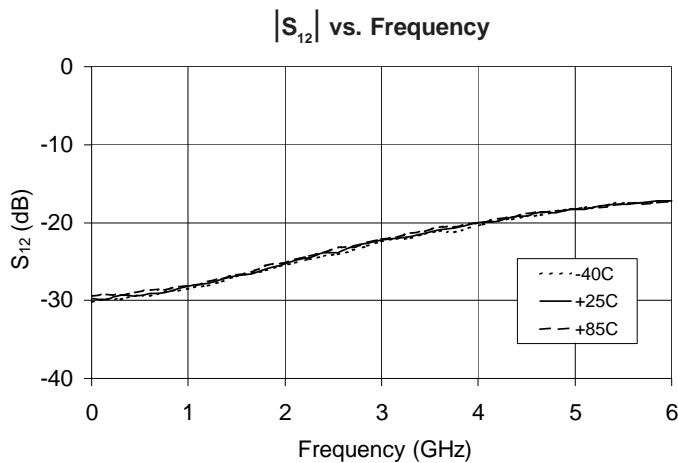
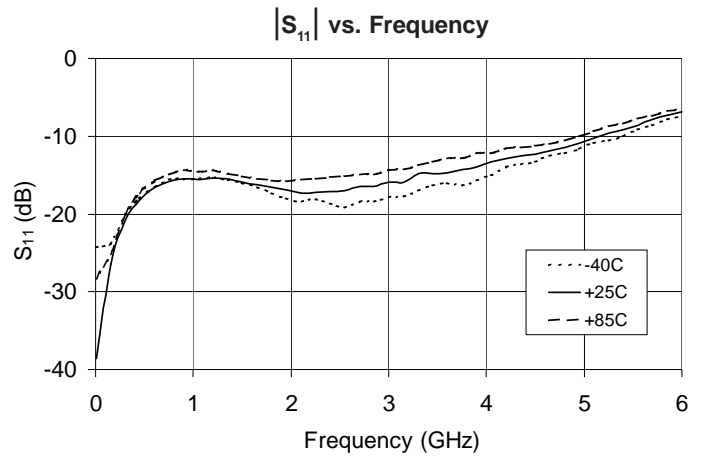
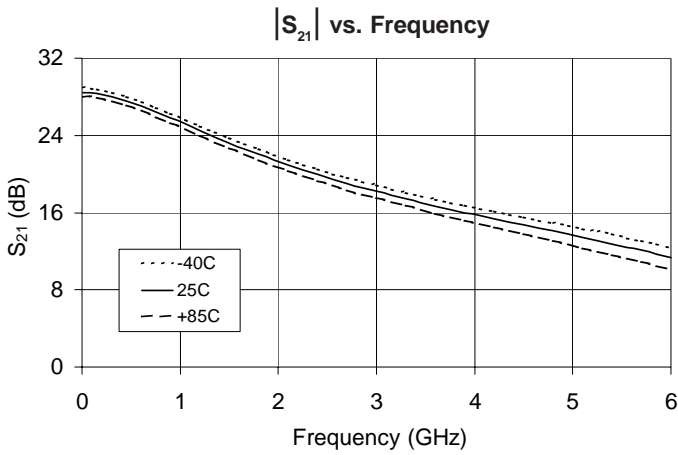


**P<sub>1dB</sub> vs. Frequency**

I<sub>b</sub> = 35 mA (Typ.)



**Typical RF Performance Over Lead Temperature -- Bias:  $I_D = 35$  mA (Typ.) at  $T_{LEAD} = +25^\circ\text{C}$**

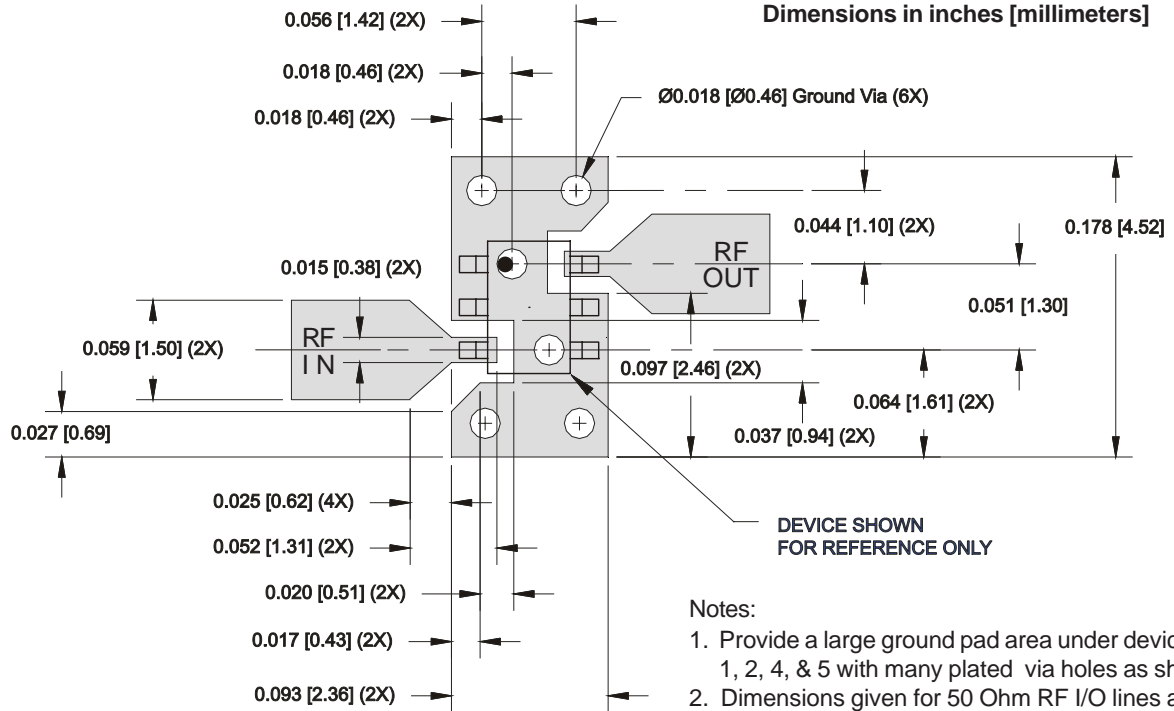


NOTE: Full S-parameter data available at [www.sirenza.com](http://www.sirenza.com)



**SOT-363 PCB Pad Layout**

Dimensions in inches [millimeters]



DEVICE SHOWN FOR REFERENCE ONLY

Notes:

1. Provide a large ground pad area under device pins 1, 2, 4, & 5 with many plated via holes as shown.
2. Dimensions given for 50 Ohm RF I/O lines are for 31 mil thick Getek. Scale accordingly for different board thicknesses and dielectric constants.
3. We recommend 1 or 2 ounce copper. Measurements for this data sheet were made on a 31 mil thick Getek with 1 ounce copper on both sides.

**SOT-363 Nominal Package Dimensions**

Dimensions in inches [millimeters]

A link to the SOT-363 package outline drawing with full dimensions and tolerances may be found on the product web page at [www.sirenza.com](http://www.sirenza.com).

